

128K x 32, 128K x 36, 256K x 18 4 Mb SYNCHRONOUS FLOW-THROUGH STATIC RAM

FEBRUARY 2014

FEATURES

- Internal self-timed write cycle
- Individual Byte Write Control and Global Write
- Clock controlled, registered address, data and control
- Burst sequence control using MODE input
- Three chip enable option for simple depth expansion and address pipelining
- Common data inputs and data outputs
- Auto Power-down during deselect
- Single cycle deselect
- Snooze MODE for reduced-power standby
- Power Supply
LF: $V_{DD} \ 3.3V \pm 5\%$, $V_{DDQ} \ 3.3V/2.5V \pm 5\%$
VF: $V_{DD} \ 2.5V -5\% +10\%$, $V_{DDQ} \ 2.5V -5\% +10\%$
- JEDEC 100-Pin QFP, 119-pin BGA, and 165-pin BGA packages
- Automotive temperature available
- Lead-free available

DESCRIPTION

The *ISSI* IS61(64)LF12832A, IS64VF12832A, IS61(64)LF/VF12836A and IS61(64)LF/VF25618A are high-speed, low-power synchronous static RAMs designed to provide burstable, high-performance memory for communication and networking applications. The IS61(64)LF12832A is organized as 131,072 words by 32 bits. The IS61(64)LF/VF12836A is organized as 131,072 words by 36 bits. The IS61(64)LF/VF25618A is organized as 262,144 words by 18 bits. Fabricated with *ISSI*'s advanced CMOS technology, the device integrates a 2-bit burst counter, high-speed SRAM core, and high-drive capability outputs into a single monolithic circuit. All synchronous inputs pass through registers controlled by a positive-edge-triggered single clock input.

Write cycles are internally self-timed and are initiated by the rising edge of the clock input. Write cycles can be one to four bytes wide as controlled by the write control inputs.

Separate byte enables allow individual bytes to be written. Byte write operation is performed by using byte write enable ($\overline{BWE}$) input combined with one or more individual byte write signals ($\overline{BWx}$). In addition, Global Write ($\overline{GW}$) is available for writing all bytes at one time, regardless of the byte write controls.

Bursts can be initiated with either $\overline{ADSP}$ (Address Status Processor) or $\overline{ADSC}$ (Address Status Cache Controller) input pins. Subsequent burst addresses can be generated internally and controlled by the $\overline{ADV}$ (burst address advance) input pin.

The mode pin is used to select the burst sequence order, Linear burst is achieved when this pin is tied LOW. Interleave burst is achieved when this pin is tied HIGH or left floating.

FAST ACCESS TIME

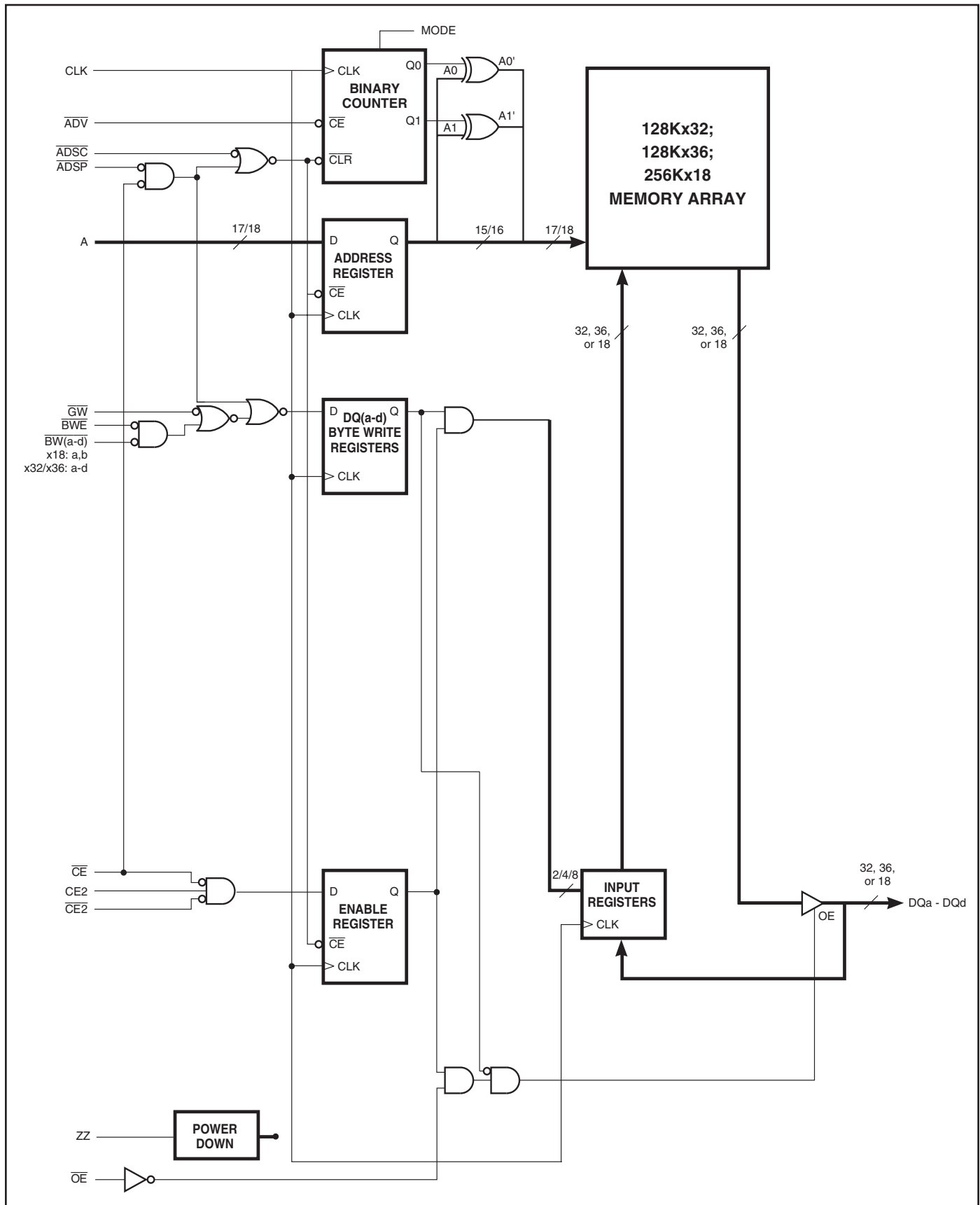
Symbol	Parameter	-6.5	-7.5	Units
tkQ	Clock Access Time	6.5	7.5	ns
tkC	Cycle Time	7.5	8.5	ns
	Frequency	133	117	MHz

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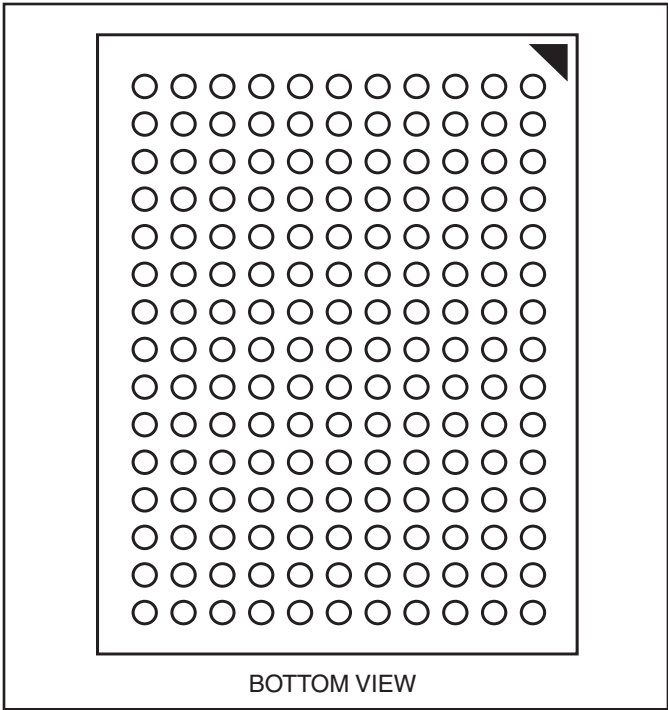
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BLOCK DIAGRAM



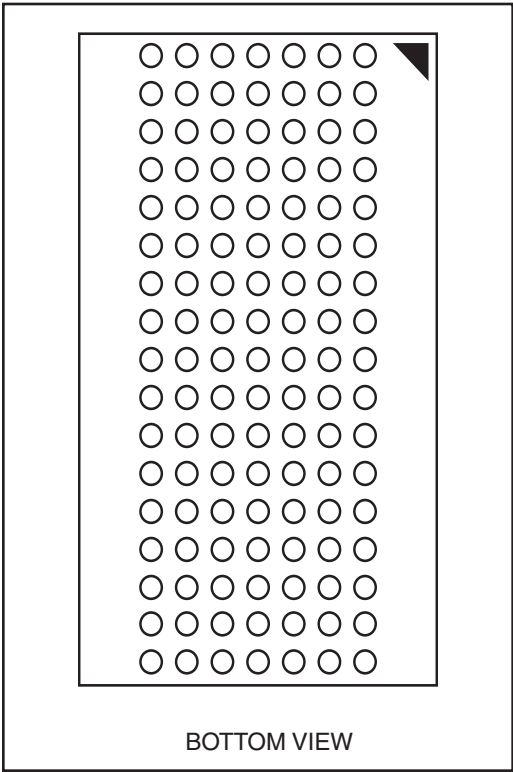
165-PIN BGA

165-Ball, 13x15 mm BGA



119-PIN BGA

119-Ball, 14x22 mm BGA



119 BGA PACKAGE PIN CONFIGURATION

128K x 36 (TOP VIEW)

	1	2	3	4	5	6	7
A	V _{DDQ}	A	A	$\overline{\text{ADSP}}$	A	A	V _{DDQ}
B	NC	CE2	A	$\overline{\text{ADSC}}$	A	$\overline{\text{CE2}}$	NC
C	NC	A	A	V _{DD}	A	A	NC
D	DQc	DQPc	Vss	NC	Vss	DQPb	DQb
E	DQc	DQc	Vss	$\overline{\text{CE}}$	Vss	DQb	DQb
F	V _{DDQ}	DQc	Vss	$\overline{\text{OE}}$	Vss	DQb	V _{DDQ}
G	DQc	DQc	$\overline{\text{BWc}}$	$\overline{\text{ADV}}$	$\overline{\text{BWb}}$	DQb	DQb
H	DQc	DQc	Vss	$\overline{\text{GW}}$	Vss	DQb	DQb
J	V _{DDQ}	V _{DD}	NC	V _{DD}	NC	V _{DD}	V _{DDQ}
K	DQd	DQd	Vss	CLK	Vss	DQa	DQa
L	DQd	DQd	$\overline{\text{BWd}}$	NC	$\overline{\text{BWa}}$	DQa	DQa
M	V _{DDQ}	DQd	Vss	$\overline{\text{BWE}}$	Vss	DQa	V _{DDQ}
N	DQd	DQd	Vss	A ₁ *	Vss	DQa	DQa
P	DQd	DQPd	Vss	A ₀ *	Vss	DQPa	DQa
R	NC	A	MODE	V _{DD}	NC	A	NC
T	NC	NC	A	A	A	NC	ZZ
U	V _{DDQ}	NC	NC	NC	NC	NC	V _{DDQ}

Note: * A₀ and A₁ are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

Symbol	Pin Name
A	Address Inputs
A0, A1	Synchronous Burst Address Inputs
$\overline{\text{ADV}}$	Synchronous Burst Address Advance
$\overline{\text{ADSP}}$	Address Status Processor
$\overline{\text{ADSC}}$	Address Status Controller
$\overline{\text{GW}}$	Global Write Enable
CLK	Synchronous Clock
$\overline{\text{CE}}$, CE2, $\overline{\text{CE2}}$	Synchronous Chip Select
$\overline{\text{BWx}}$ (x=a-d)	Synchronous Byte Write Controls
$\overline{\text{BWE}}$	Byte Write Enable

Symbol	Pin Name
$\overline{\text{OE}}$	Output Enable
ZZ	Power Sleep Mode
MODE	Burst Sequence Selection
NC	No Connect
DQa-DQd	Data Inputs/Outputs
DQPa-Pd	Output Power Supply
V _{DD}	Power Supply
V _{DDQ}	Output Power Supply
Vss	Ground

119 BGA PACKAGE PIN CONFIGURATION

256Kx18 (TOP VIEW)

	1	2	3	4	5	6	7
A	V _{DDQ}	A	A	$\overline{\text{ADSP}}$	A	A	V _{DDQ}
B	NC	CE2	A	$\overline{\text{ADSC}}$	A	$\overline{\text{CE2}}$	NC
C	NC	A	A	V _{DD}	A	A	NC
D	DQb	NC	V _{SS}	NC	V _{SS}	DQP _a	NC
E	NC	DQb	V _{SS}	$\overline{\text{CE}}$	V _{SS}	NC	DQ _a
F	V _{DDQ}	NC	V _{SS}	$\overline{\text{OE}}$	V _{SS}	DQ _a	V _{DDQ}
G	NC	DQb	$\overline{\text{BWb}}$	$\overline{\text{ADV}}$	V _{SS}	NC	DQ _a
H	DQb	NC	V _{SS}	$\overline{\text{GW}}$	V _{SS}	DQ _a	NC
J	V _{DDQ}	V _{DD}	NC	V _{DD}	NC	V _{DD}	V _{DDQ}
K	NC	DQb	V _{SS}	CLK	V _{SS}	NC	DQ _a
L	DQb	NC	V _{SS}	NC	$\overline{\text{BWa}}$	DQ _a	NC
M	V _{DDQ}	DQb	V _{SS}	$\overline{\text{BWE}}$	V _{SS}	NC	V _{DDQ}
N	DQb	NC	V _{SS}	A ₁ *	V _{SS}	DQ _a	NC
P	NC	DQP _b	V _{SS}	A ₀ *	V _{SS}	NC	DQ _a
R	NC	A	MODE	V _{DD}	NC	A	NC
T	NC	A	A	NC	A	A	ZZ
U	V _{DDQ}	NC	NC	NC	NC	NC	V _{DDQ}

Note: * A₀ and A₁ are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

Symbol	Pin Name
A	Address Inputs
A ₀ , A ₁	Synchronous Burst Address Inputs
$\overline{\text{ADV}}$	Synchronous Burst Address Advance
$\overline{\text{ADSP}}$	Address Status Processor
$\overline{\text{ADSC}}$	Address Status Controller
$\overline{\text{GW}}$	Global Write Enable
CLK	Synchronous Clock
$\overline{\text{CE}}$, CE2, $\overline{\text{CE2}}$	Synchronous Chip Select
$\overline{\text{BWx}}$ (x=a,b)	Synchronous Byte Write Controls
$\overline{\text{BWE}}$	Byte Write Enable

Symbol	Pin Name
$\overline{\text{OE}}$	Output Enable
ZZ	Power Sleep Mode
MODE	Burst Sequence Selection
NC	No Connect
DQ _a -DQ _b	Data Inputs/Outputs
DQP _a -P _b	Output Power Supply
V _{DD}	Power Supply
V _{DDQ}	Output Power Supply
V _{SS}	Ground

165 BGA PACKAGE PIN CONFIGURATION

128K x 36 (TOP VIEW)

	1	2	3	4	5	6	7	8	9	10	11
A	NC	A	$\overline{CE}$	BWc	BWb	CE2	$\overline{BWE}$	ADSC	$\overline{ADV}$	A	NC
B	NC	A	CE2	$\overline{BWd}$	$\overline{BWa}$	CLK	$\overline{GW}$	$\overline{OE}$	$\overline{ADSP}$	A	NC
C	DQPc	NC	VDDQ	Vss	Vss	Vss	Vss	Vss	VDDQ	NC	DQPb
D	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
E	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
F	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
G	DQc	DQc	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQb	DQb
H	NC	NC	NC	VDD	Vss	Vss	Vss	VDD	NC	NC	ZZ
J	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
K	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
L	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
M	DQd	DQd	VDDQ	VDD	Vss	Vss	Vss	VDD	VDDQ	DQa	DQa
N	DQPd	NC	VDDQ	Vss	NC	NC	NC	Vss	VDDQ	NC	DQPa
P	NC	NC	A	A	NC	A1*	NC	A	A	A	NC
R	MODE	NC	A	A	NC	A0*	NC	A	A	A	A

Note: * A0 and A1 are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

Symbol	Pin Name
A	Address Inputs
A0, A1	Synchronous Burst Address Inputs
$\overline{ADV}$	Synchronous Burst Address Advance
$\overline{ADSP}$	Address Status Processor
$\overline{ADSC}$	Address Status Controller
$\overline{GW}$	Global Write Enable
CLK	Synchronous Clock
$\overline{CE}$, $\overline{CE2}$, CE2	Synchronous Chip Select
$\overline{BWx}$ (x=a,b,c,d)	Synchronous Byte Write Controls

Symbol	Pin Name
$\overline{BWE}$	Byte Write Enable
$\overline{OE}$	Output Enable
ZZ	Power Sleep Mode
MODE	Burst Sequence Selection
NC	No Connect
DQx	Data Inputs/Outputs
DQPx	Data Inputs/Outputs
VDD	3.3V/2.5V Power Supply
VDDQ	Isolated Output Power Supply 3.3V/2.5V
Vss	Ground

165 BGA PACKAGE PIN CONFIGURATION

256K x 18 (TOP VIEW)

	1	2	3	4	5	6	7	8	9	10	11
A	NC	A	$\overline{CE}$	$\overline{BWb}$	NC	$\overline{CE2}$	$\overline{BWE}$	$\overline{ADSC}$	ADV	A	A
B	NC	A	CE2	NC	$\overline{BWa}$	CLK	$\overline{GW}$	$\overline{OE}$	$\overline{ADSP}$	A	NC
C	NC	NC	V _{DDQ}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{SS}	V _{DDQ}	NC	DQP _a
D	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
E	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
F	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
G	NC	DQ _b	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	NC	DQ _a
H	NC	NC	NC	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	NC	NC	ZZ
J	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
K	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
L	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
M	DQ _b	NC	V _{DDQ}	V _{DD}	V _{SS}	V _{SS}	V _{SS}	V _{DD}	V _{DDQ}	DQ _a	NC
N	DQP _b	NC	V _{DDQ}	V _{SS}	NC	NC	NC	V _{SS}	V _{DDQ}	NC	NC
P	NC	NC	A	A	NC	A ₁ *	NC	A	A	A	NC
R	MODE	NC	A	A	NC	A ₀ *	NC	A	A	A	A

Note: * A₀ and A₁ are the two least significant bits (LSB) of the address field and set the internal burst counter if burst is desired.

PIN DESCRIPTIONS

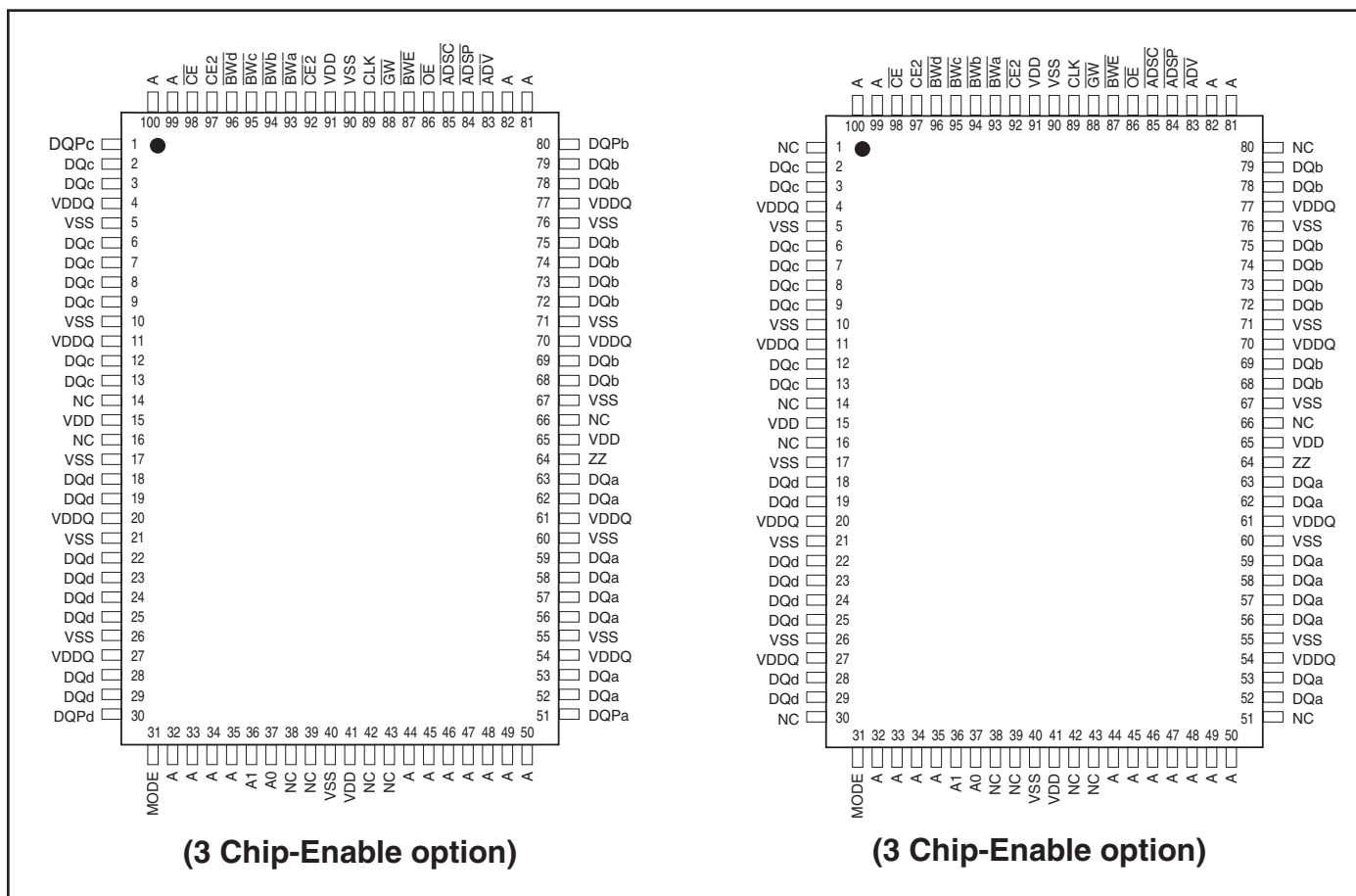
Symbol	Pin Name
A	Address Inputs
A ₀ , A ₁	Synchronous Burst Address Inputs
ADV	Synchronous Burst Address Advance
$\overline{ADSP}$	Address Status Processor
$\overline{ADSC}$	Address Status Controller
$\overline{GW}$	Global Write Enable
CLK	Synchronous Clock
$\overline{CE}$, $\overline{CE2}$, CE2	Synchronous Chip Select
$\overline{BWx}$ (x=a,b)	Synchronous Byte Write Controls

Symbol	Pin Name
$\overline{BWE}$	Byte Write Enable
$\overline{OE}$	Output Enable
ZZ	Power Sleep Mode
MODE	Burst Sequence Selection
NC	No Connect
DQ _x	Data Inputs/Outputs
DQP _x	Data Inputs/Outputs
V _{DD}	3.3V/2.5V Power Supply
V _{DDQ}	Isolated Output Power Supply 3.3V/2.5V
V _{SS}	Ground

PIN CONFIGURATION

100-PIN QFP (128K x 36)

100-PIN QFP (128K x 32)



PIN DESCRIPTIONS

A0, A1	Synchronous Address Inputs. These pins must tied to the two LSBs of the address bus.
A	Synchronous Address Inputs
ADSC	Synchronous Controller Address Status
ADSP	Synchronous Processor Address Status
ADV	Synchronous Burst Address Advance
BW _a -BW _d	Synchronous Byte Write Enable
BWE	Synchronous Byte Write Enable
CE, CE2, CE2	Synchronous Chip Enable
CLK	Synchronous Clock

DQa-DQd	Synchronous Data Input/Output
DQPa-DQPd	Parity Data Input/Output
GW	Synchronous Global Write Enable
MODE	Burst Sequence Mode Selection
OE	Output Enable
VDD	3.3V/2.5V Power Supply
VDDQ	Isolated Output Buffer Supply: 3.3V/2.5V
Vss	Ground
ZZ	Snooze Enable

TRUTH TABLE⁽¹⁻⁸⁾

OPERATION	ADDRESS	$\overline{CE}$	$\overline{CE2}$	$\overline{CE2}$	$\overline{ZZ}$	$\overline{ADSP}$	$\overline{ADSC}$	$\overline{ADV}$	$\overline{WRITE}$	$\overline{OE}$	CLK	DQ
Deselect Cycle, Power-Down	None	H	X	X	L	X	L	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	X	L	L	L	X	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	H	X	L	L	X	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	X	L	L	H	L	X	X	X	L-H	High-Z
Deselect Cycle, Power-Down	None	L	H	X	L	H	L	X	X	X	L-H	High-Z
Snooze Mode, Power-Down	None	X	X	X	H	X	X	X	X	X	X	High-Z
Read Cycle, Begin Burst	External	L	L	H	L	L	X	X	X	L	L-H	Q
Read Cycle, Begin Burst	External	L	L	H	L	L	X	X	X	H	L-H	High-Z
Write Cycle, Begin Burst	External	L	L	H	L	H	L	X	L	X	L-H	D
Read Cycle, Begin Burst	External	L	L	H	L	H	L	X	H	L	L-H	Q
Read Cycle, Begin Burst	External	L	L	H	L	H	L	X	H	H	L-H	High-Z
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	X	X	X	L	H	H	L	H	H	L-H	High-Z
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	L	L-H	Q
Read Cycle, Continue Burst	Next	H	X	X	L	X	H	L	H	H	L-H	High-Z
Write Cycle, Continue Burst	Next	X	X	X	L	H	H	L	L	X	L-H	D
Write Cycle, Continue Burst	Next	H	X	X	L	X	H	L	L	X	L-H	D
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	H	H	L-H	High-Z
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	L	L-H	Q
Read Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	H	H	L-H	High-Z
Write Cycle, Suspend Burst	Current	X	X	X	L	H	H	H	L	X	L-H	D
Write Cycle, Suspend Burst	Current	H	X	X	L	X	H	H	L	X	L-H	D

NOTE:

1. X means "Don't Care." H means logic HIGH. L means logic LOW.
2. For $\overline{WRITE}$, L means one or more byte write enable signals ($\overline{BWA-d}$) and $\overline{BWE}$ are LOW or $\overline{GW}$ is LOW. $\overline{WRITE} = H$ for all $\overline{BWx}$, $\overline{BWE}$, $\overline{GW}$ HIGH.
3. $\overline{BWA}$ enables WRITES to DQa's and DQPa. $\overline{BWb}$ enables WRITES to DQb's and DQPb. $\overline{BWc}$ enables WRITES to DQc's and DQPC. $\overline{BWD}$ enables WRITES to DQd's and DQPD. DQPa and DQPb are available on the x18 version. DQPa-DQPD are available on the x36 version.
4. All inputs except $\overline{OE}$ and $\overline{ZZ}$ must meet setup and hold times around the rising edge (LOW to HIGH) of CLK.
5. Wait states are inserted by suspending burst.
6. For a WRITE operation following a READ operation, $\overline{OE}$ must be HIGH before the input data setup time and held HIGH during the input data hold time.
7. This device contains circuitry that will ensure the outputs will be in High-Z during power-up.
8. $\overline{ADSP}$ LOW always initiates an internal READ at the L-H edge of CLK. A WRITE is performed by setting one or more byte write enable signals and $\overline{BWE}$ LOW or $\overline{GW}$ LOW for the subsequent L-H edge of CLK. See WRITE timing diagram for clarification.

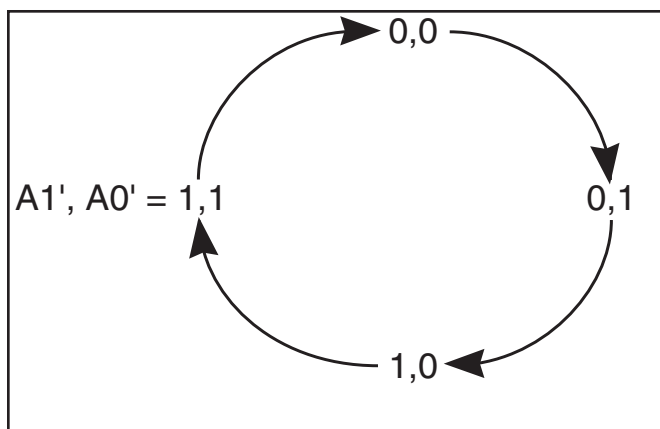
PARTIAL TRUTH TABLE

Function	$\overline{GW}$	$\overline{BWE}$	$\overline{BWA}$	$\overline{BWb}$	$\overline{BWc}$	$\overline{BWD}$
Read	H	H	X	X	X	X
Read	H	L	H	H	H	H
Write Byte 1	H	L	L	H	H	H
Write All Bytes	H	L	L	L	L	L
Write All Bytes	L	X	X	X	X	X

INTERLEAVED BURST ADDRESS TABLE (MODE = V_{DD} or No Connect)

External Address A1 A0	1st Burst Address A1 A0	2nd Burst Address A1 A0	3rd Burst Address A1 A0
00	01	10	11
01	00	11	10
10	11	00	01
11	10	01	00

LINEAR BURST ADDRESS TABLE (MODE = V_{SS})



ABSOLUTE MAXIMUM RATINGS⁽¹⁾

Symbol	Parameter	Value	Unit
T _{STG}	Storage Temperature	−55 to +150	°C
P _D	Power Dissipation	1.6	W
I _{OUT}	Output Current (per I/O)	100	mA
V _{IN} , V _{OUT}	Voltage Relative to V _{SS} for I/O Pins	−0.5 to V _{DDQ} + 0.5	V
V _{IN}	Voltage Relative to V _{SS} for for Address and Control Inputs	−0.5 to V _{DD} + 0.5	V
V _{DD}	Voltage on V _{DD} Supply Relative to V _{SS}	−0.5 to 4.6	V

Notes:

1. Stress greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. This device contains circuitry to protect the inputs against damage due to high static voltages or electric fields; however, precautions may be taken to avoid application of any voltage higher than maximum rated voltages to this high-impedance circuit.
3. This device contains circuitry that will ensure the output devices are in High-Z at power up.

OPERATING RANGE (IS61/64LFxxxxx)

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	3.3V ± 5%	3.3V/2.5V ± 5%
Industrial	-40°C to +85°C	3.3V ± 5%	3.3V/2.5V ± 5%
Automotive	-40°C to +125°C	3.3V ± 5%	3.3V/2.5V ± 5%

OPERATING RANGE (IS61/64VFxxxxx)

Range	Ambient Temperature	V _{DD}	V _{DDQ}
Commercial	0°C to +70°C	2.5V -5% +10%	2.5V -5% +10%
Industrial	-40°C to +85°C	2.5V -5% +10%	2.5V -5% +10%
Automotive	-40°C to +125°C	2.5V -5% +10%	2.5V -5% +10%

DC ELECTRICAL CHARACTERISTICS (Over Operating Range)

Symbol	Parameter	Test Conditions	3.3V		2.5V		Unit
			Min.	Max.	Min.	Max.	
V _{OH}	Output HIGH Voltage	I _{OH} = -4.0 mA (3.3V) I _{OH} = -1.0 mA (2.5V)	2.4	—	2.0	—	V
V _{OL}	Output LOW Voltage	I _{OL} = 8.0 mA (3.3V) I _{OL} = 1.0 mA (2.5V)	—	0.4	—	0.4	V
V _{IH}	Input HIGH Voltage ⁽¹⁾		2.0	V _{DD} + 0.3	1.7	V _{DD} + 0.3	V
V _{IL}	Input LOW Voltage ⁽¹⁾		-0.3	0.8	-0.3	0.7	V
I _{LI}	Input Leakage Current	V _{SS} ≤ V _{IN} ≤ V _{DD} ⁽¹⁾	-5	5	-5	5	μA
I _{LO}	Output Leakage Current	V _{SS} ≤ V _{OUT} ≤ V _{DDQ} , $\overline{OE}$ = V _{IH}	-5	5	-5	5	μA

Note:

- V_{ILL}(min) = -2.0V AC (pulse width < t_{KC}/ 2). Guaranteed by design.
 V_{IHH}(max) = V_{DD} + 1.5V AC (pulse width < t_{KC}/ 2). Guaranteed by design.

POWER SUPPLY CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	Test Conditions	Temp. range	6.5 MAX		7.5 MAX		Unit
				x18	x32/x36	x18	x32/x36	
I _{CC}	AC Operating Supply Current	Device Selected,	Com.	175	175	155	155	mA
		$\overline{OE} = V_{IH}$, $ZZ \leq V_{IL}$,	Ind.	180	180	160	160	
		All Inputs $\leq 0.2V$ or $\geq V_{DD} - 0.2V$,	Auto.	190	190	175	175	
		Cycle Time $\geq t_{KC}$ min.	typ. ⁽²⁾	120		110		
I _{SB}	Standby Current TTL Input	Device Deselected,	Com.	90	90	90	90	mA
		$V_{DD} = \text{Max.}$,	Ind.	100	100	100	100	
		All Inputs $\leq V_{IL}$ or $\geq V_{IH}$,	Auto.	120	120	120	120	
		$ZZ \leq V_{IL}$, $f = \text{Max.}$						
I _{SB1}	Standby Current CMOS Input	Device Deselected,	Com.	70	70	70	70	mA
		$V_{DD} = \text{Max.}$,	Ind.	75	75	75	75	
		$V_{IN} \leq V_{SS} + 0.2V$ or $\geq V_{DD} - 0.2V$	Auto.	90	90	90	90	
		$f = 0$	typ.	40		40		
I _{SB2}	Sleep Mode	$ZZ > V_{IH}$	Com.	30	30	30	30	mA
			Ind.	35	35	35	35	
			Auto.	45	45	45	45	
			typ.	25		25		

Note:

1. MODE pin has an internal pullup and should be tied to V_{DD} or V_{SS} . It exhibits $\pm 100 \mu A$ maximum leakage current when tied to $\leq V_{SS} + 0.2V$ or $\geq V_{DD} - 0.2V$.
2. Typical values are measured at $V_{DD} = 3.3V$, $T_A = 25^\circ C$ and not 100% tested.

CAPACITANCE^(1,2)

Symbol	Parameter	Conditions	Max.	Unit
C _{IN}	Input Capacitance	$V_{IN} = 0V$	6	pF
C _{OUT}	Input/Output Capacitance	$V_{OUT} = 0V$	8	pF

Notes:

1. Tested initially and after any design or process changes that may affect these parameters.
2. Test conditions: $T_A = 25^\circ C$, $f = 1 \text{ MHz}$, $V_{DD} = 3.3V$.

3.3V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 3.0V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.5V
Output Load	See Figures 1 and 2

AC TEST LOADS

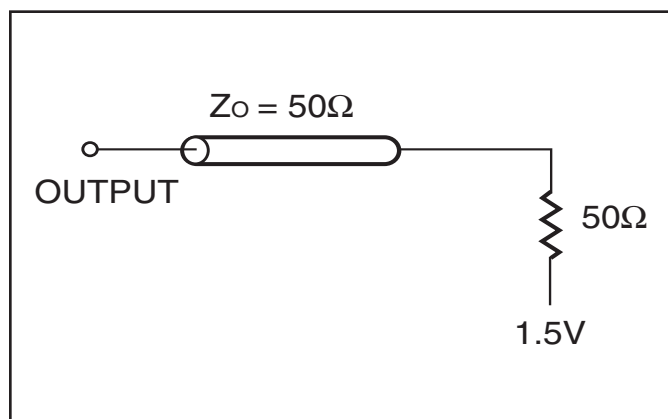


Figure 1

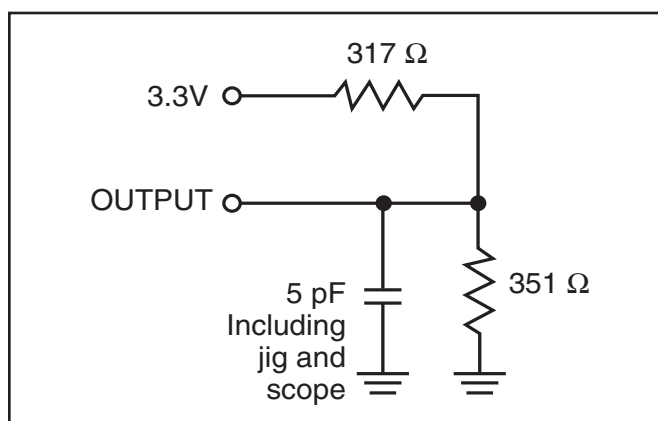


Figure 2

2.5V I/O AC TEST CONDITIONS

Parameter	Unit
Input Pulse Level	0V to 2.5V
Input Rise and Fall Times	1.5 ns
Input and Output Timing and Reference Level	1.25V
Output Load	See Figures 3 and 4

2.5V I/O OUTPUT LOAD EQUIVALENT

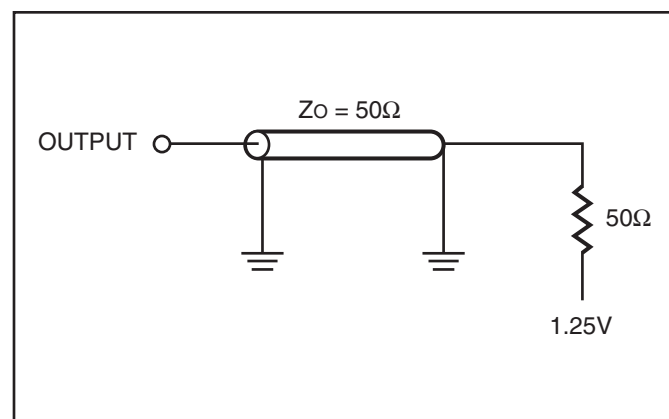


Figure 3

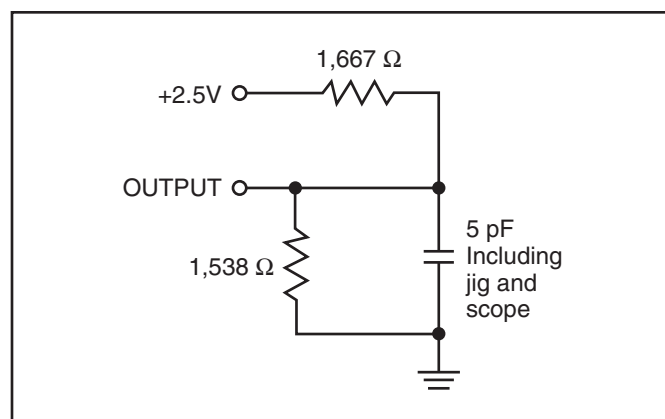


Figure 4

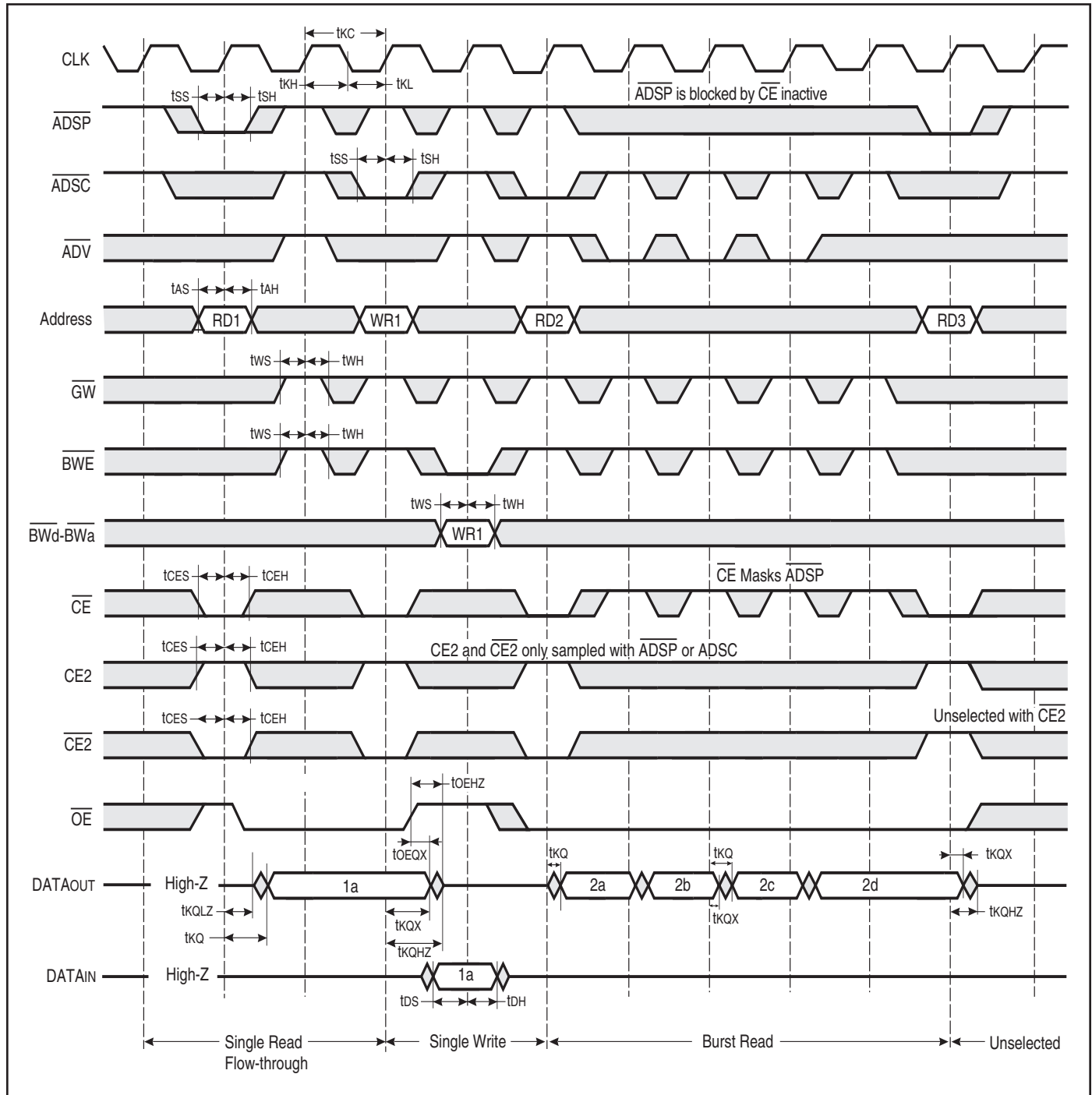
READ/WRITE CYCLE SWITCHING CHARACTERISTICS⁽¹⁾ (Over Operating Range)

Symbol	Parameter	6.5		7.5		Unit
		Min.	Max.	Min.	Max.	
fmax	Clock Frequency	—	133	—	117	MHz
t _{KC}	Cycle Time	7.5	—	8.5	—	ns
t _{KH}	Clock High Time	2.2	—	2.5	—	ns
t _{KL}	Clock Low Time	2.2	—	2.5	—	ns
t _{KQ}	Clock Access Time	—	6.5	—	7.5	ns
t _{KQX} ⁽²⁾	Clock High to Output Invalid	2.5	—	2.5	—	ns
t _{KQLZ} ^(2,3)	Clock High to Output Low-Z	2.5	—	2.5	—	ns
t _{KQHZ} ^(2,3)	Clock High to Output High-Z	—	3.8	—	4.0	ns
t _{OEQ}	Output Enable to Output Valid	—	3.2	—	3.4	ns
t _{OEQX} ⁽²⁾	Output Enable to Output Invalid	2.5	—	2.5	—	ns
t _{OELZ} ^(2,3)	Output Enable to Output Low-Z	0	—	0	—	ns
t _{OEHZ} ^(2,3)	Output Disable to Output High-Z	—	3.5	—	3.5	ns
t _{AS}	Address Setup Time	1.5	—	1.5	—	ns
t _{SS}	Address Status Setup Time	1.5	—	1.5	—	ns
t _{WS}	Read/Write Setup Time	1.5	—	1.5	—	ns
t _{CES}	Chip Enable Setup Time	1.5	—	1.5	—	ns
t _{AVS}	Address Advance Setup Time	1.5	—	1.5	—	ns
t _{DS}	Data Setup Time	1.5	—	1.5	—	ns
t _{AH}	Address Hold Time	0.5	—	0.5	—	ns
t _{WH}	Write Hold Time	0.5	—	0.5	—	ns
t _{SH}	Address Status Hold Time	0.5	—	0.5	—	ns
t _{CEH}	Chip Enable Hold Time	0.5	—	0.5	—	ns
t _{AVH}	Address Advance Hold Time	0.5	—	0.5	—	ns
t _{DH}	Data Hold Time	0.5	—	0.5	—	ns
t _{PDS}	ZZ High to Power Down	—	2	—	2	cyc
t _{PUS}	ZZ Low to Power Down	—	2	—	2	cyc

Notes:

1. Configuration signal MODE is static and must not change during normal operation.
2. Guaranteed but not 100% tested. This parameter is periodically sampled.
3. Tested with load in Figure 2.

READ/WRITE CYCLE TIMING

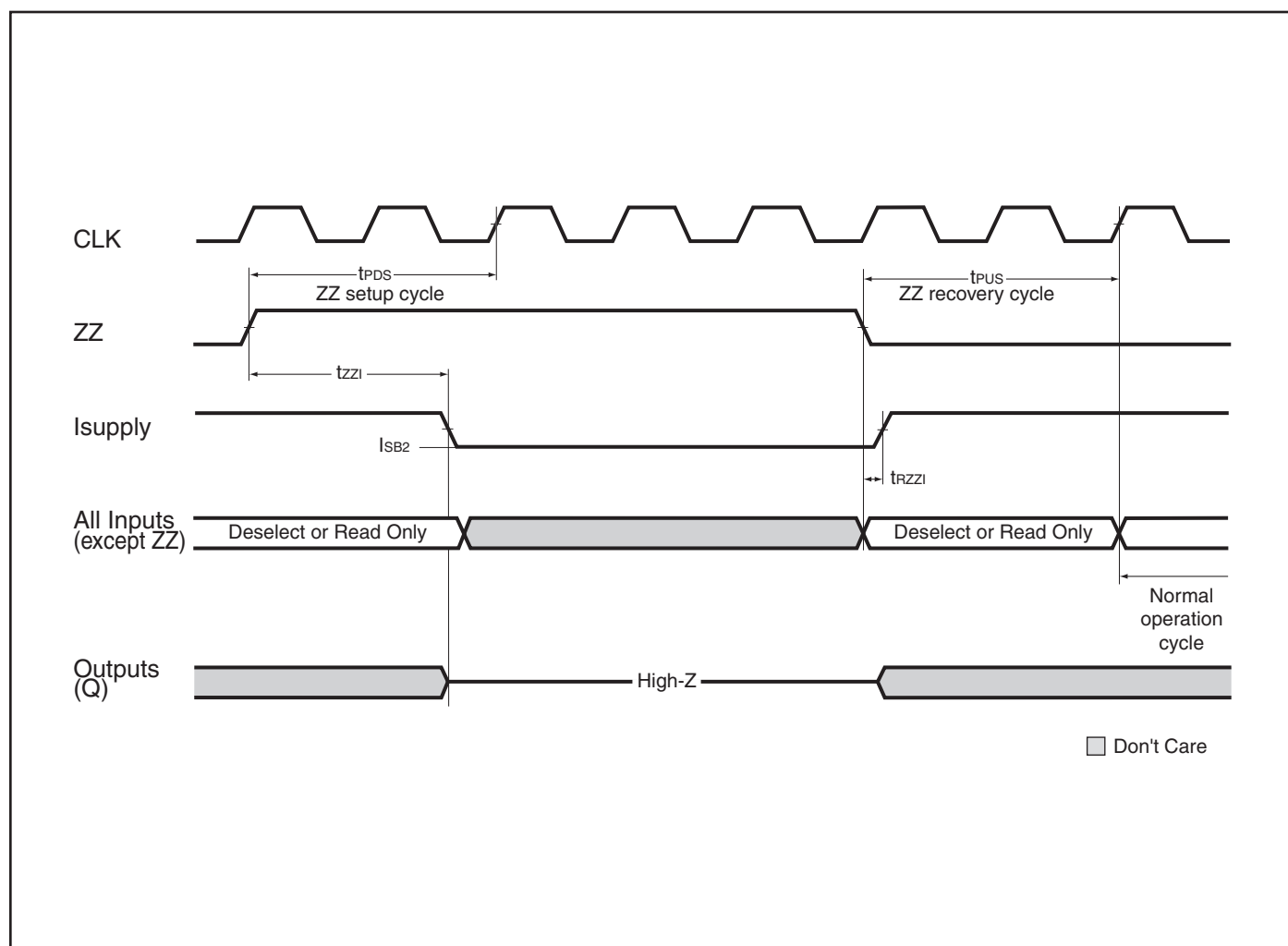


The diagram illustrates the timing relationships for the ADSP signal. The signals shown are CLK, ADSP, ADSC, ADV, Address, GW, BWE, BWd-BWa, CE, CE2, CE2, OE, DATAOUT, and DATAIN. The diagram is divided into four main sections: Single Write, Burst Write, Write, and Unselected. Key timing parameters are labeled, including t_{SS}, t_{SH}, t_{K1}, t_{KL}, t_{AVS}, t_{AVH}, t_{AS}, t_{AH}, t_{WS}, t_{WH}, t_{CES}, t_{CEH}, t_{DS}, and t_{DH}. Annotations include 'ADSP is blocked by CE1 inactive', 'ADSC initiate Write', 'ADV must be inactive for ADSP Write', 'CE1 Masks ADSP', 'CE2 and CE3 only sampled with ADSP or ADSC', 'Unselected with CE2', and 'BW4-BW1 only are applied to first cycle of WR2'.

SNOOZE MODE ELECTRICAL CHARACTERISTICS

Symbol	Parameter	Conditions	Min.	Max.	Unit
ISB2	Current during SNOOZE MODE	$ZZ \geq V_{ih}$	—	60	mA
tpDS	ZZ active to input ignored		—	2	cycle
tpUS	ZZ inactive to input sampled		2	—	cycle
tzZI	ZZ active to SNOOZE current		—	2	cycle
trZZI	ZZ inactive to exit SNOOZE current		0	—	ns

SNOOZE MODE TIMING



ORDERING INFORMATION ($V_{DD} = 3.3V/V_{DDQ} = 2.5V/3.3V$)

Commercial Range: 0°C to +70°C

Configuration	Access Time	Order Part Number	Package
128Kx32	6.5	IS61LF12832A-6.5TQ	100 QFP
		IS61LF12832A-6.5B2	119 BGA
		IS61LF12832A-6.5B3	165 BGA
128Kx32	7.5	IS61LF12832A-7.5TQ	100 QFP
		IS61LF12832A-7.5B2	119 BGA
		IS61LF12832A-7.5B3	165 BGA
128Kx36	6.5	IS61LF12836A-6.5TQ	100 QFP
		IS61LF12836A-6.5B2	119 BGA
		IS61LF12836A-6.5B3	165 BGA
128Kx36	7.5	IS61LF12836A-7.5TQ	100 QFP
		IS61LF12836A-7.5B2	119 BGA
		IS61LF12836A-7.5B3	165 BGA
256Kx18	6.5	IS61LF25618A-6.5TQ	100 QFP
		IS61LF25618A-6.5TQL	100 QFP, Lead-free
		IS61LF25618A-6.5B2	119 BGA
		IS61LF25618A-6.5B3	165 BGA
256Kx18	7.5	IS61LF25618A-7.5TQ	100 QFP
		IS61LF25618A-7.5B2	119 BGA
		IS61LF25618A-7.5B3	165 BGA

ORDERING INFORMATION ($V_{DD} = 3.3V/V_{DDQ} = 2.5V/3.3V$)

Industrial Range: -40°C to +85°C

Configuration	Access Time	Order Part Number	Package
128Kx32	6.5	IS61LF12832A-6.5TQI	100 QFP
		IS61LF12832A-6.5B2I	119 BGA
		IS61LF12832A-6.5B3I	165 BGA
128Kx32	7.5	IS61LF12832A-7.5TQI	100 QFP
		IS61LF12832A-7.5TQLI	100 QFP, Lead-free
		IS61LF12832A-7.5B2I	119 BGA
		IS61LF12832A-7.5B3I	165 BGA
128Kx36	6.5	IS61LF12836A-6.5TQI	100 QFP
		IS61LF12836A-6.5TQLI	100 QFP, Lead-free
		IS61LF12836A-6.5B2I	119 BGA
		IS61LF12836A-6.5B3I	165 BGA
128Kx36	7.5	IS61LF12836A-7.5TQI	100 QFP
		IS61LF12836A-7.5TQLI	100 QFP, Lead-free
		IS61LF12836A-7.5B2I	119 BGA
		IS61LF12836A-7.5B3I	165 BGA
256Kx18	6.5	IS61LF25618A-6.5TQI	100 QFP
		IS61LF25618A-6.5B2I	119 BGA
		IS61LF25618A-6.5B3I	165 BGA
256Kx18	7.5	IS61LF25618A-7.5TQI	100 QFP
		IS61LF25618A-7.5TQLI	100 QFP, Lead-free
		IS61LF25618A-7.5B2I	119 BGA
		IS61LF25618A-7.5B3I	165 BGA

Automotive Range: -40°C to +125°C

Configuration	Access Time	Order Part Number	Package
128Kx32	7.5	IS64LF12832A-7.5TQA3	100 QFP
		IS64LF12832A-7.5TQLA3	100 QFP, Lead-free
128Kx36	7.5	IS64LF12836A-7.5TQA3	100 QFP
		IS64LF12836A-7.5B3LA3	165 BGA, Lead-free
256Kx18	7.5	IS64LF25618A-7.5TQA3	100 QFP

ORDERING INFORMATION ($V_{DD} = 2.5V$ / $V_{DDQ} = 2.5V$)

Commercial Range: 0°C to +70°C

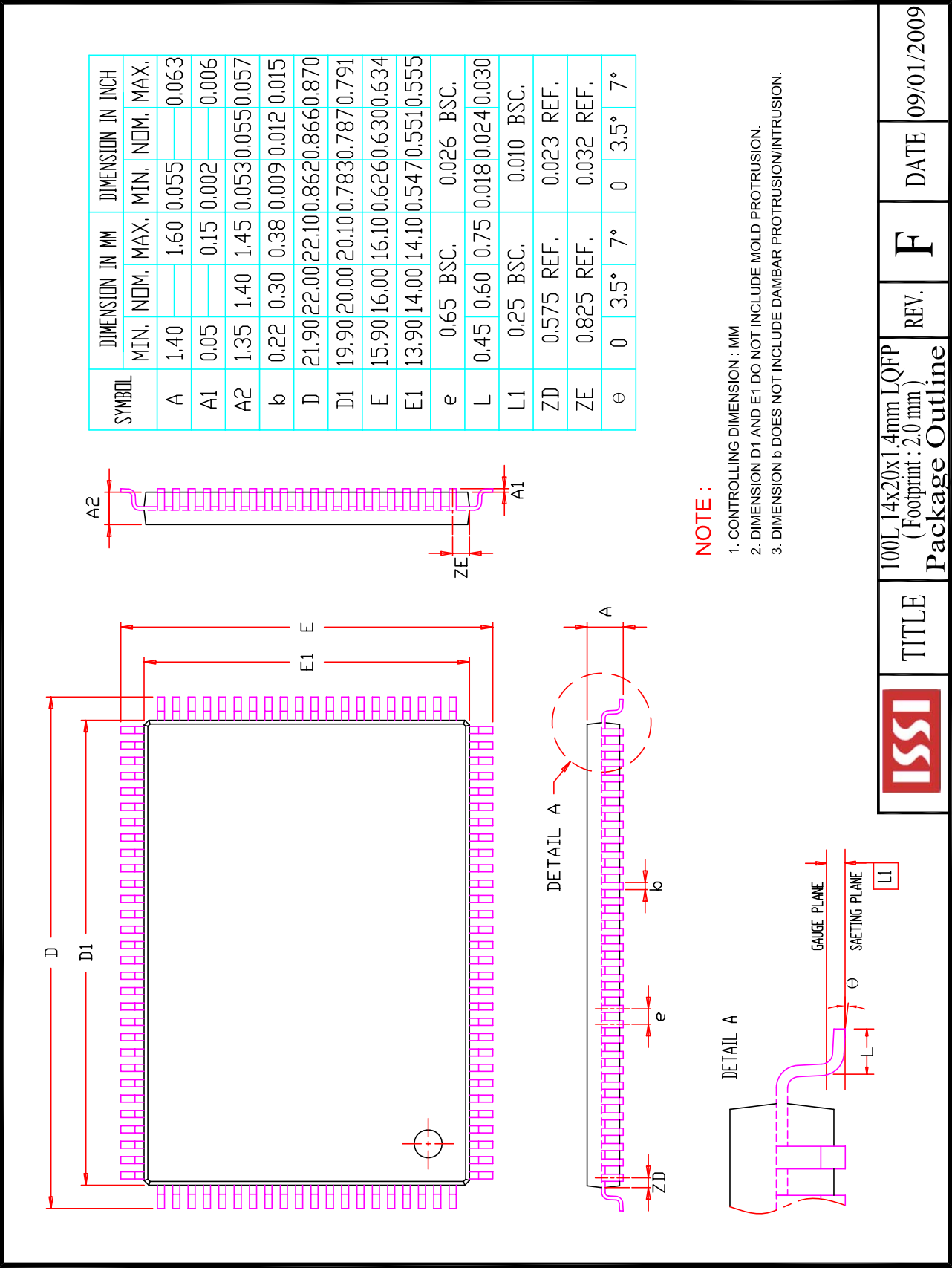
Configuration	Access Time	Order Part Number	Package
128Kx36	6.5	IS61VF12836A-6.5TQ	100 QFP
		IS61VF12836A-6.5B2	119 BGA
		IS61VF12836A-6.5B3	165 BGA
128Kx36	7.5	IS61VF12836A-7.5TQ	100 QFP
		IS61VF12836A-7.5B2	119 BGA
		IS61VF12836A-7.5B3	165 BGA
256Kx18	6.5	IS61VF25618A-6.5TQ	100 QFP
		IS61VF25618A-6.5B2	119 BGA
		IS61VF25618A-6.5B3	165 BGA
256Kx18	7.5	IS61VF25618A-7.5TQ	100 QFP
		IS61VF25618A-7.5B2	119 BGA
		IS61VF25618A-7.5B3	165 BGA

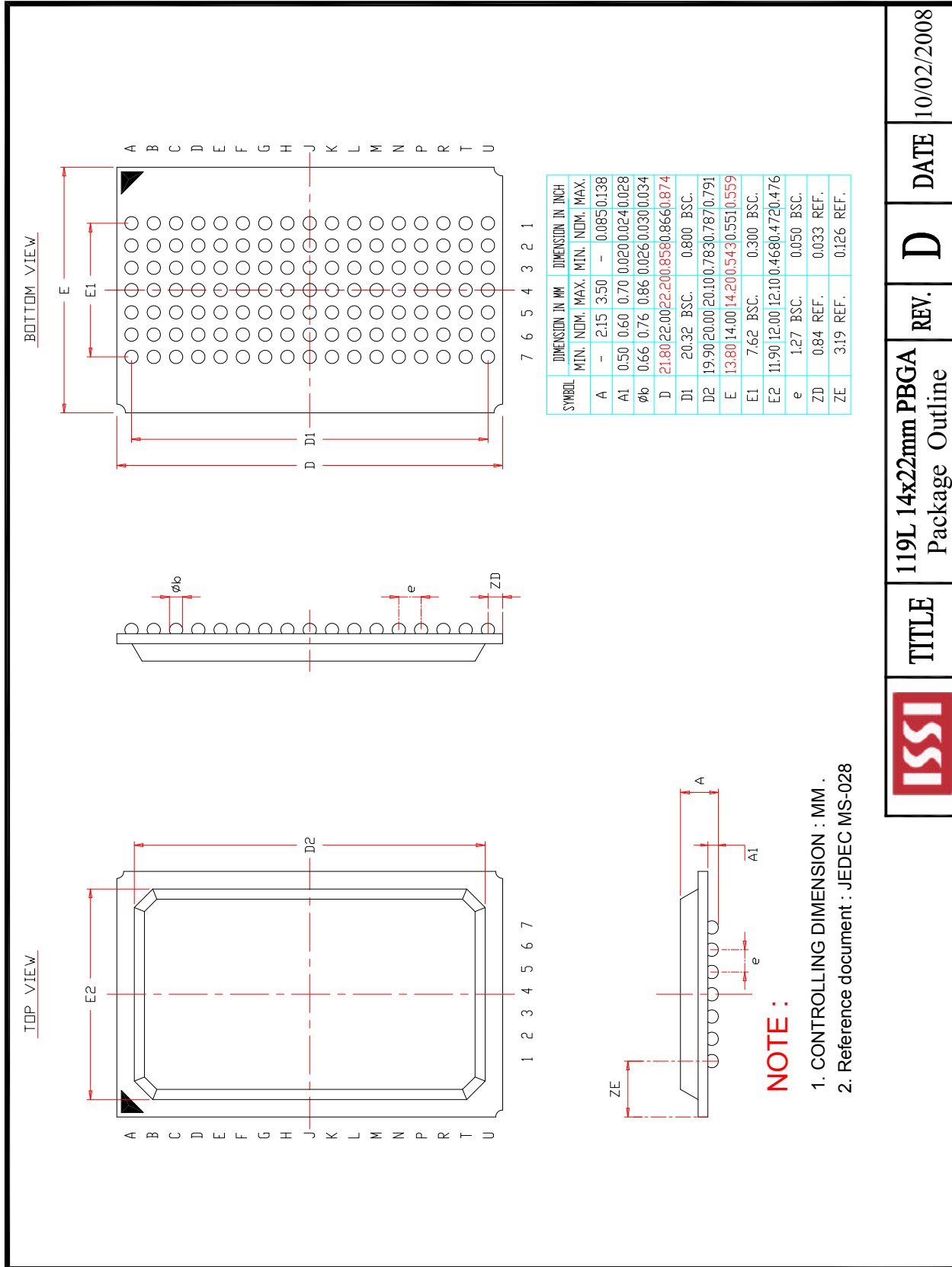
Industrial Range: -40°C to +85°C

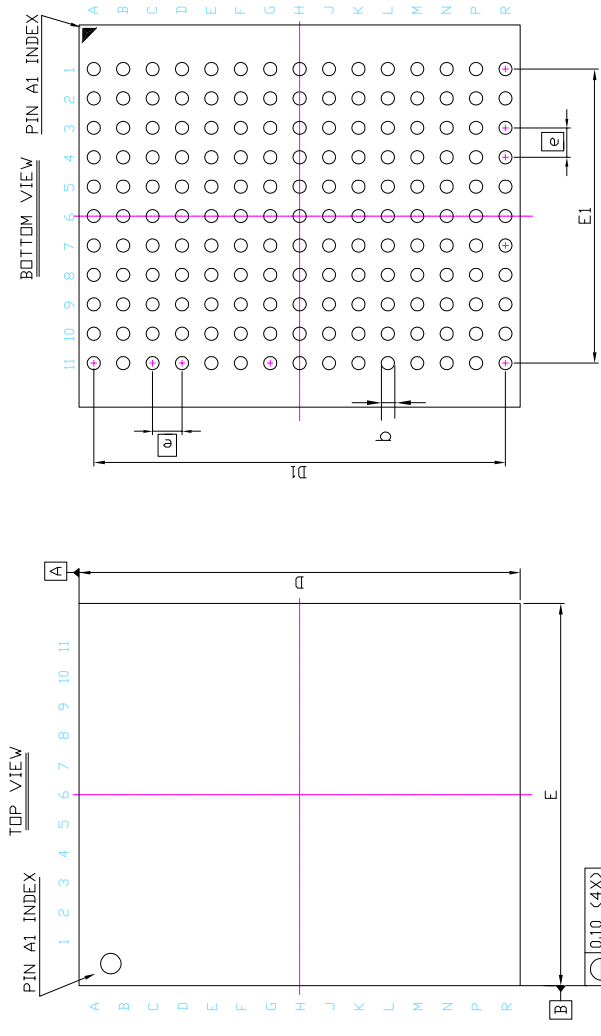
Configuration	Access Time	Order Part Number	Package
128Kx36	6.5	IS61VF12836A-6.5TQI	100 QFP
		IS61VF12836A-6.5B2I	119 BGA
		IS61VF12836A-6.5B3I	165 BGA
128Kx36	7.5	IS61VF12836A-7.5TQI	100 QFP
		IS61VF12836A-7.5B2I	119 BGA
		IS61VF12836A-7.5B3I	165 BGA
256Kx18	6.5	IS61VF25618A-6.5TQI	100 QFP
		IS61VF25618A-6.5B2I	119 BGA
		IS61VF25618A-6.5B3I	165 BGA
256Kx18	7.5	IS61VF25618A-7.5TQI	100 QFP
		IS61VF25618A-7.5B2I	119 BGA
		IS61VF25618A-7.5B3I	165 BGA

Automotive Range: -40°C to +125°C

Configuration	Access Time	Order Part Number	Package
128Kx32	7.5	IS64VF12832A-7.5TQLA3	100 QFP, Lead-free
128Kx36	7.5	IS64VF12836A-7.5TQA3	100 QFP
256Kx18	7.5	IS64VF25618A-7.5TQA3	100 QFP

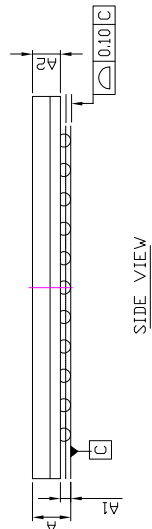






SYM.	DIMENSION (mm)			DIMENSION (inch)		
	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
A	—	—	1.20	—	—	0.047
A1	0.25	0.35	0.40	0.010	0.014	0.016
A2	—	0.79	—	—	0.031	—
b	0.40	0.45	0.50	0.016	0.018	0.020
D	14.90	15.00	15.10	0.587	0.591	0.594
D1	13.90	14.00	14.10	0.547	0.551	0.555
E	12.90	13.00	13.10	0.508	0.512	0.516
E1	9.90	10.00	10.10	0.390	0.394	0.398
E1	1.00 BSC			0.039 BSC		

NOTE :
1. CONTROLLING DIMENSION : MM .



ISSI	TITLE	165L 13x15mm TF-BGA Package Outline	REV.	B	DATE	08/28/2008
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